SEMITRONICS CORP.

M50-100-XX-06 to 16 SERIES

THREE PHASE BRIDGE

Features

- Low V F
- | Direct Mounting to heatsink
- Low profile package
- | Glass Passivation Chip
- Easy Connection
- | Insulated Type

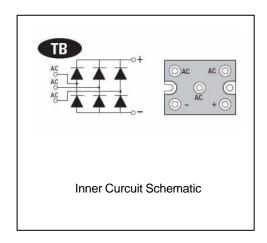
Typical Applications

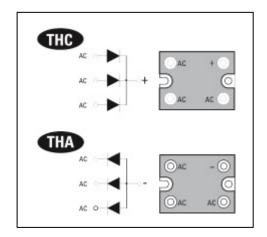
- Inverters
- | Welding
- | UPS
- | SMPS
- Battery Chargers
- DC Motors
- General Purpose DC Power Supplies

Major Ratings and Characteristics

Parameters		M50-100-XX-XX	Units
I ₀		100	Α
	@ T c	85	°C
I _{FSM}	@ 50Hz	1500	Α
	@ 60Hz	1450	А
I²t	@ 50Hz	1140	A ² s
	@ 60Hz	1050	A ² s
V _{DRM} /V _{RRM}		400 to 2000	V
T J	range	- 40 to 150	℃

3-Phase Rectifier Series





M50-100-XX-06 to 16 SERIES

ELECTRICAL SPECIFICATIONS

Voltage Ratings

	Voltage	V_{RRM}/V_{DRM} , maximum repetitive	V _{RSM} , maximum non-	I _{RRM} /I _{DRM} max
Type number	Code	peak reverse voltage	repetitive peak rev. voltage	@ T J = T J max
		V	V	mA
M50-100	06	600	700	
	08	800	900	
	12	1200	1300	5
	14	1400	1500	
	16	1600	1700	

Forward Conduction

	Parameter	M50-100-XX -04-16	Units	Conditions		
Ιο	Maximum DC output current	100	Α	120° Rect conduction angle		
	@ Case temperature	80	°C			
I _{FSM} ,	Maximum peak, one-cycle	1500	Α	t = 10ms	No voltage	
	forward, non-repetitive	1450		t = 8.3ms	reapplied	
	on state surge current	1300		t = 10ms	100% V _{RRM}	
		1220		t = 8.3ms	reapplied	Initia
I ² t	Maximum I 2 t for fusing	1140	A ² s	t = 10ms	No voltage	T」=T」 max.
		1050		t = 8.3ms	reapplied	
		700		t = 10ms	100% V _{RRM}	
		650		t = 8.3ms	reapplied	
I ² v t	Maximum I ² v t for fusing	114000	A ² v s	t = 0.1 to 10ms, no voltage reapplied		
V _{FM}	Maximum forward voltage drop	1.20	V	pk = 100A, T_J = 25°C, t p = 400 μ s single junction		

Insulation Table

Parameter	M50-100-TB -600.	Units	Conditions
V _{INS} RMS insulation voltage	2500	٧	T = 25 $_{\circ}$ C all terminal shorted f = 50Hz, t = 1s

M50-100-XX-04 to 16 SERIES

Thermal and Mechanical Specifications

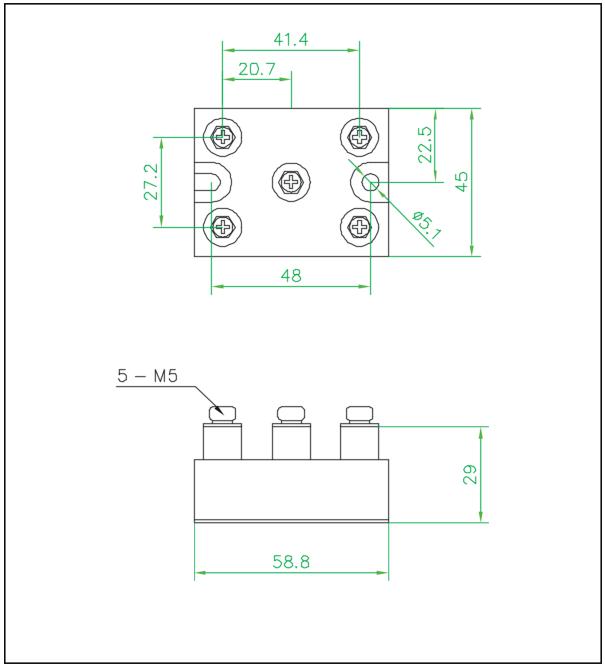
	Parameter	M50-100-TB -600.	Units	Conditions
TJ	Maximum junction operating temperature range	- 40 to 150	°C	
T _{stg}	Maximum storage temperature range	- 40 to 125	°C	
R_{thJC}	Maximum thermal resistance,	0.3	KW	DC operation per module
	junction to case	1.80		DC operation per junction
		0.35		120° Rect condunction angle per module
		2.20		120° Rect condunction angle per junction
R _{th} JC	Maximum I ² v t for fusing	0.04	KW	Per module. Mounting surface smooth, flat and greased. Heatsink compound thermal conductivity = 0.42W/mK
Т	Mounting torque ± 10% to heatsink	4	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.Lubricated threads.
wt	Approximate weight	196	g	

Part Number Identification

Series Type	Current	Circuit Type	Voltage	
M50	100	See Schematic diagram	06 (600v) 14 (1400V)	
	(100Amps)	TB, THA, THC	08 (800V) 16 (1600V)	
			12 (1200V)	

M50-100-XX-04 to 16 SERIES

Package Outline (max. dimensions in mm)



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